MOSFETs Silicon P-Channel MOS (U-MOSVI)

TJ60S04M3L

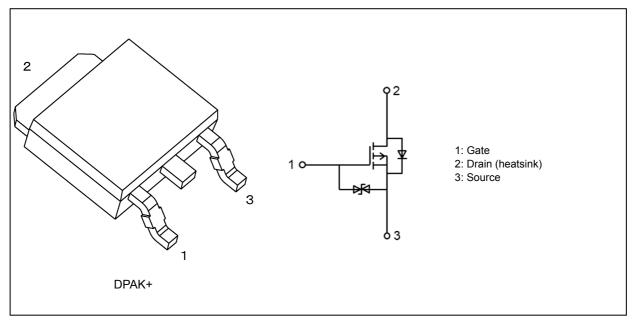
1. Applications

- Automotive
- Motor Drivers
- DC-DC Converters
- Switching Voltage Regulators

2. Features

- (1) AEC-Q101 qualified
- (2) Low drain-source on-resistance: $R_{DS(ON)} = 4.8 \text{ m}\Omega$ (typ.) ($V_{GS} = -10 \text{ V}$)
- (3) Low leakage current: $I_{\rm DSS}$ = -10 μA (max) (V_{\rm DS} = -40 V)
- (4) Enhancement mode: V_{th} = -2.0 to -3.0 V (V_{DS} = -10 V, I_D = -1 mA)

3. Packaging and Internal Circuit



4. Absolute Maximum Ratings (Note) ($T_a = 25^{\circ}C$ unless otherwise specified)

| Characteristics | | | | Rating | Unit |
|-------------------------------|-------------------------|----------|------------------|------------|------|
| Drain-source voltage | | | V _{DSS} | -40 | V |
| Gate-source voltage | | | V _{GSS} | -20/+10 | 1 |
| Drain current (DC) | | (Note 1) | Ι _D | -60 | Α |
| Drain current (pulsed) | | (Note 1) | I _{DP} | -120 | |
| Power dissipation | (T _c = 25°C) | | PD | 90 | W |
| Single-pulse avalanche energy | | (Note 2) | E _{AS} | 146 | mJ |
| Avalanche current | | | I _{AR} | -60 | Α |
| Channel temperature | | (Note 3) | T _{ch} | 175 | °C |
| Storage temperature | | (Note 3) | T _{stg} | -55 to 175 | |

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

5. Thermal Characteristics

| Characteristics | Symbol | Max | Unit |
|------------------------------------|-----------------------|------|------|
| Channel-to-case thermal resistance | R _{th(ch-c)} | 1.65 | °C/W |

Note 1: Ensure that the channel temperature does not exceed 175°C.

Note 2: V_DD = -25 V, T_ch = 25°C (initial), L = 42 $\mu H, R_G$ = 25 Ω, I_{AR} = -60 A

Note 3: The definitions of the absolute maximum channel and storage temperatures are qualified per AEC-Q101.

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

6. Electrical Characteristics

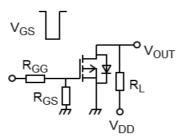
6.1. Static Characteristics ($T_a = 25^{\circ}C$ unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|---|----------------------|--|------|------|------|------|
| Gate leakage current | I _{GSS} | V _{GS} = -16/+10 V, V _{DS} = 0 V | _ | _ | ±10 | μA |
| Drain cut-off current | I _{DSS} | V_{DS} = -40 V, V_{GS} = 0 V | _ | _ | -10 | |
| Drain-source breakdown voltage | V _{(BR)DSS} | I _D = -10 mA, V _{GS} = 0 V | -40 | — | _ | V |
| Drain-source breakdown voltage (Note 4) | V _{(BR)DSX} | I _D = -10 mA, V _{GS} = 10 V | -30 | _ | _ | |
| Gate threshold voltage | V _{th} | V _{DS} = -10 V, I _D = -1 mA | -2.0 | _ | -3.0 | |
| Drain-source on-resistance | R _{DS(ON)} | V _{GS} = -6 V, I _D = -30 A | | 6.1 | 9.4 | mΩ |
| | | V _{GS} = -10 V, I _D = -30 A | _ | 4.8 | 6.3 | |

Note 4: If a forward bias is applied between gate and source, this device enters V_{(BR)DSX} mode. Note that the drainsource breakdown voltage is lowered in this mode.

6.2. Dynamic Characteristics ($T_a = 25^{\circ}C$ unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|--------------------------------|------------------|---|-----|------|-----|------|
| Input capacitance | C _{iss} | V _{DS} = -10 V, V _{GS} = 0 V, f = 1 MHz | _ | 6510 | _ | pF |
| Reverse transfer capacitance | C _{rss} | | — | 570 | — | |
| Output capacitance | C _{oss} | | | 780 | _ | |
| Switching time (rise time) | t _r | See Figure 6.2.1. | | 96 | — | ns |
| Switching time (turn-on time) | t _{on} | | | 126 | — | |
| Switching time (fall time) | t _f | | | 240 | _ | |
| Switching time (turn-off time) | t _{off} | | | 730 | _ | |



$$\begin{split} &V_{DD}\approx -20 \ V \\ &V_{GS}=0 \ V/-10 \ V \\ &I_{D}=-30 \ A \\ &R_{L}=0.67 \ \Omega \\ &R_{GG}=R_{GS}=4.7 \ \Omega \\ &Duty\leq 1 \ \%, \ t_{w}=10 \ \mu s \end{split}$$

Fig. 6.2.1 Switching Time Test Circuit

6.3. Gate Charge Characteristics ($T_a = 25^{\circ}C$ unless otherwise specified)

| Characteristics | Symbol | Test Condition | Min | Тур. | Max | Unit |
|---|-----------------|--|-----|------|-----|------|
| Total gate charge (gate-source plus gate-drain) | Qg | $V_{DD}\approx$ -32 V, V_{GS} = -10 V, I_{D} = -60 A | — | 125 | — | nC |
| Gate-source charge | Q _{gs} | | _ | 81 | _ | |
| Gate-drain charge | Q _{gd} | | _ | 44 | _ | |

6.4. Source-Drain Characteristics ($T_a = 25^{\circ}C$ unless otherwise specified)

| Characteristics | | Symbol | Test Condition | Min | Тур. | Max | Unit |
|--------------------------------|----------|------------------|--|-----|------|------|------|
| Reverse drain current (DC) | (Note 5) | I _{DR} | — | _ | | -60 | А |
| Reverse drain current (pulsed) | (Note 5) | I _{DRP} | — | _ | | -120 | |
| Diode forward voltage | | V _{DSF} | I _{DR} = -60 A, V _{GS} = 0 V | _ | | 1.2 | V |
| Reverse recovery time | | t _{rr} | I _{DR} = -60 A, V _{GS} = 0 V | _ | 45 | _ | ns |
| Reverse recovery charge | | Q _{rr} | dl _{DR} /dt = 50 A/µs | _ | 27 | _ | nC |

Note 5: Ensure that the channel temperature does not exceed 175°C.

7. Marking (Note)

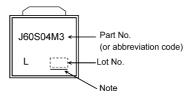


Fig. 7.1 Marking

 Note:
 A line under a Lot No. identifies the indication of product Labels.

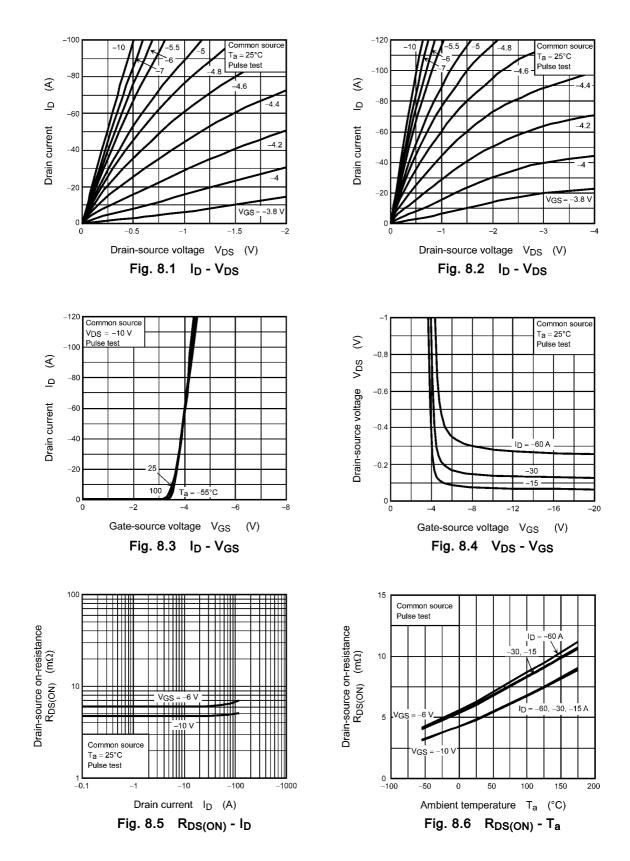
 Not underlined:
 [[Pb]]/INCLUDES > MCV

 Underlined:
 [[G]]/RoHS COMPATIBLE or [[G]]/RoHS [[Pb]]

 Please contact your TOSHIBA sales representative for details as to environmental matters such as the RoHS compatibility of Product.

 The RoHS is the Directive 2011/65/EU of the European Parliament and of the Council of 8 June 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment.

8. Characteristics Curves (Note)



S

_3

-2

-1

0 _100

-50

0

50

Ambient temperature Ta (°C)

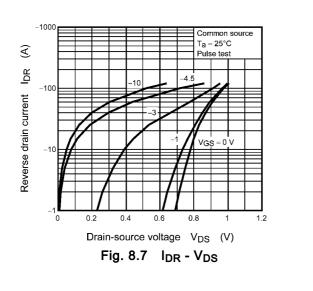
Fig. 8.9 V_{th} - T_a

100

150

200

Gate threshold voltage



Common source $V_{DS} = -10 V$ $I_{D} = -1 mA$

Pulse test

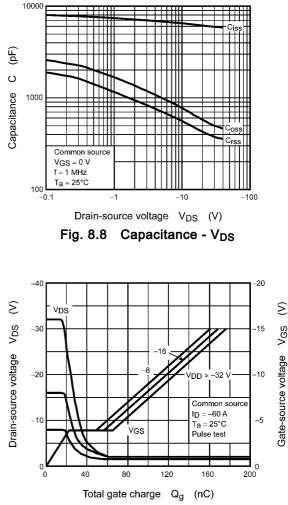
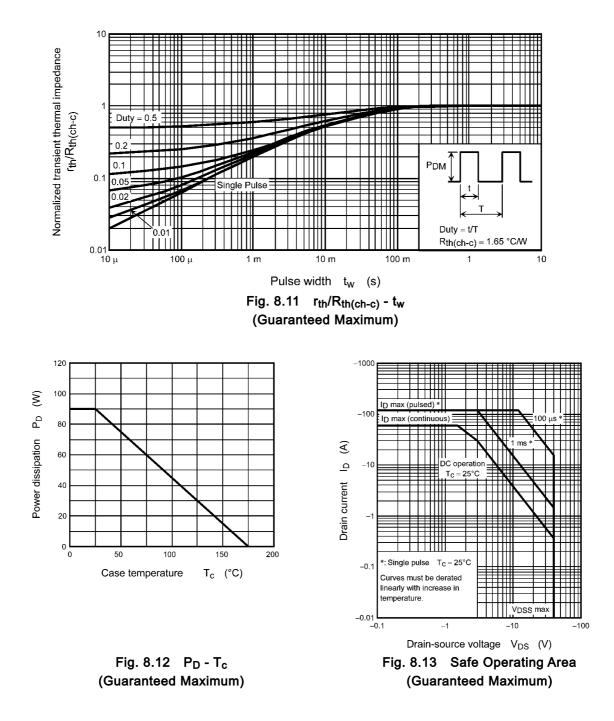


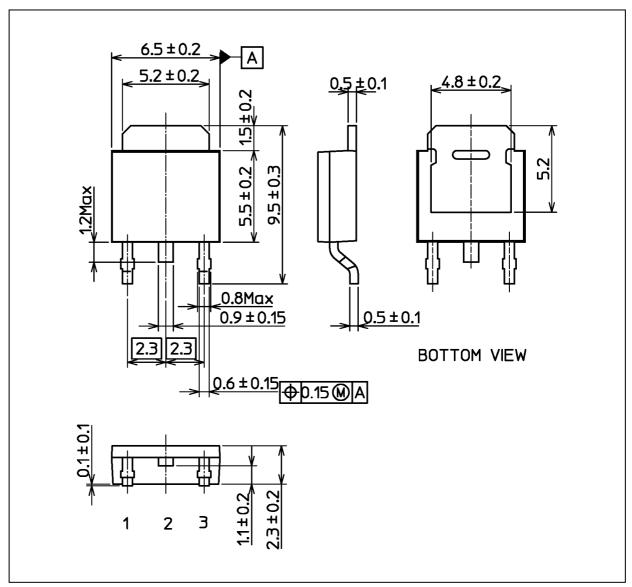
Fig. 8.10 Dynamic Input/Output Characteristics



Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

Package Dimensions

Unit: mm



Weight: 0.36 g (typ.)

| | Package Name(s) |
|-----------------|-----------------|
| TOSHIBA: 2-7M1A | |
| Nickname: DPAK+ | |

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